



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

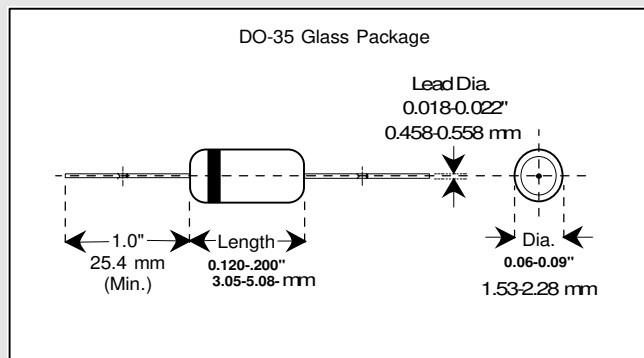


Applications

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability



Maximum Ratings	Symbol	Value	Unit	
Peak Inverse Voltage	PIV	85 (Min).	Volts	
Average Rectified Current	I _{avg}	200	mAmps	
Continuous Forward Current	I _{Fdc}	200	mAmps	
Peak Surge Current (t _{peak} = 1 sec.)	I _{peak}	1.0	Amp	
BKC Power Dissipation T _L =50 °C, L = 3/8" from body	P _{tot}	500	mWatts	
Operating Temperature Range	T _{Op}	-65 to +200	° C	
Storage Temperature Range	T _{St}	-65 to +200	° C	
Electrical Characteristics @ 25 °C*	Symbol	Minimum	Maximum	Unit
Forward Voltage Drop @ I _F = 400 mA	V _F	***	1.10	Volts
Breakdown Voltage @ I _R = 25 μA	PIV	85		Volts
Reverse Leakage Current @ V _R = 50 V	I _R		100	μA
Reverse Recovery time (note 1)	t _{rr}		10	nSecs

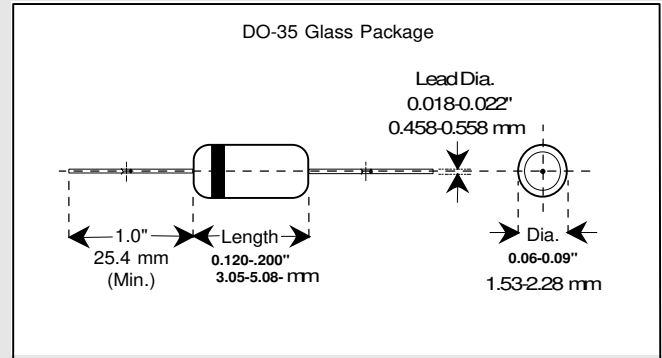
Note 1: Per Method 4031-A with I_F = 10 mA, V_r = 6 V, R_L = 100 Ohms. * UNLESS OTHERWISE SPECIFIED

Applications

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Features

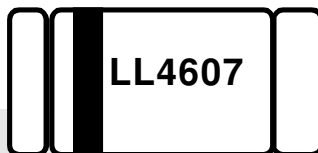
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Peak Inverse Voltage	PIV	85 (Min).	Volts	
Average Rectified Current	I_{avg}	200	mAmps	
Continuous Forward Current	I_{Fdc}	500	mAmps	
Peak Surge Current ($t_{peak} = 1 \text{ sec.}$)	I_{peak}	1.0	Amp	
BKC Power Dissipation $T_L = 50^\circ\text{C}$, $L = 3/8"$ from body	P_{tot}	500	mWatts	
Operating Temperature Range	T_{Op}	-65 to +150	$^\circ\text{C}$	
Storage Temperature Range	T_{St}	-65 to +150	$^\circ\text{C}$	
Electrical Characteristics @ 25 $^\circ\text{C}$ *	Symbol	Minimum	Maximum	Unit
Forward Voltage Drop @ $I_F = 400 \text{ mA}$	V_F	***	1.10	Volts
Breakdown Voltage @ $I_R = 25 \mu\text{A}$	PIV	85		Volts
Reverse Leakage Current @ $V_R = 50 \text{ V}$	I_R		100	μA
Reverse Recovery time (note 1)	t_{rr}		10	nSecs

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Silicon Switching Diode



LL4607

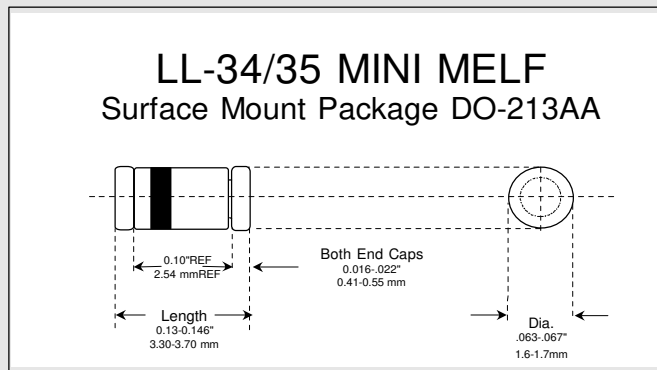
L-35 Glass Package

Applications

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

Features

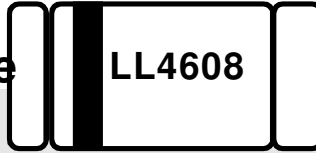
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Maximum Ratings		Symbol	Value	Unit	
Peak Inverse Voltage		PIV	85 (Min).	Volts	
Average Rectified Current		I_{avg}	200	mAmps	
Continuous Forward Current		I_{Fdc}	200	mAmps	
Peak Surge Current ($t_{peak} = 1 \text{ sec.}$)		I_{peak}	1.0	Amp	
BKC Power Dissipation		P_{tot}	500	mWatts	
Operating Temperature Range		T_{Op}	-65 to +200	°C	
Storage Temperature Range		T_{St}	-65 to +200	°C	
Electrical Characteristics @ 25 °C*		Symbol	Minimum	Maximum	Unit
Forward Voltage Drop @ $I_F = 400 \text{ mA}$		V_F	***	1.10	Volts
Breakdown Voltage @ $I_R = 25 \mu\text{A}$		PIV	85		Volts
Reverse Leakage Current @ $V_R = 50 \text{ V}$		I_R		100	μA
Reverse Recovery time (note 1)		t_{rr}		10	nSecs

Note 1: Per Method 4031-A with $I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $R_L = 100 \text{ Ohms}$. * UNLESS OTHERWISE SPECIFIED

Silicon Switching Diode



LL4608

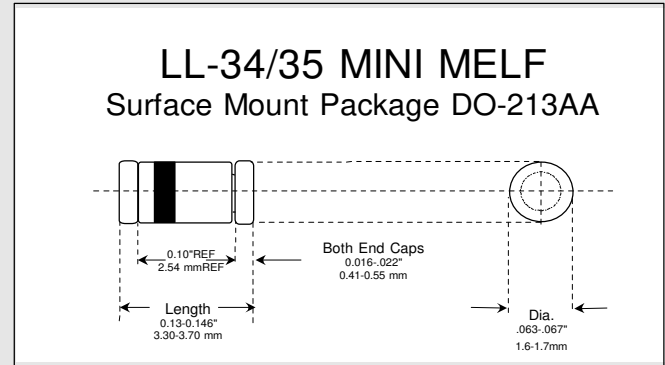
LL-35 Glass Package

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Microsemi

6 Lake Street - Lawrence, MA 01841

Tel: 978-681-0392 - Fax: 978-681-9135